



BSS138AKA

60 V, single N-channel Trench MOSFET

29 April 2015

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	-	200	mA
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 100\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_j = 25\text{ }^{\circ}\text{C}$		-	2.7	4.5	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

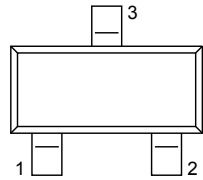
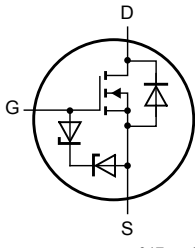


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-236AB (SOT23)	 017aaa255
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS138AKA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code
BSS138AKA	%JL

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	200	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	125	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	800	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	300	mW
			[1]	-	360	mW
		T _{sp} = 25 °C		-	1060	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	200	mA

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

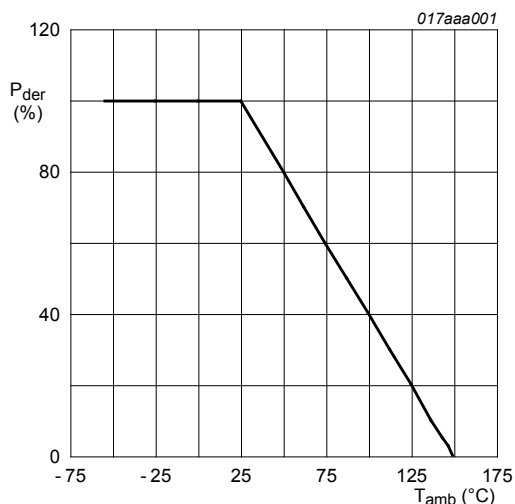


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

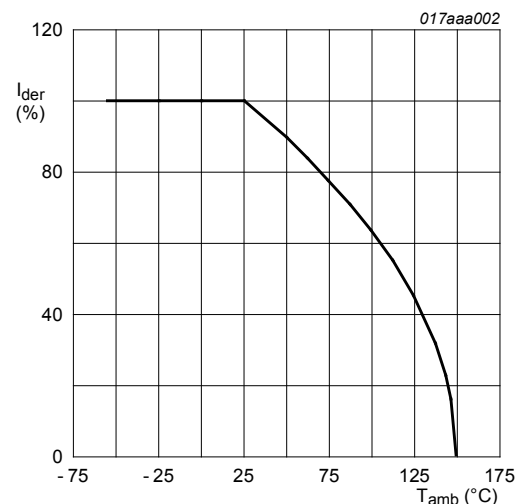
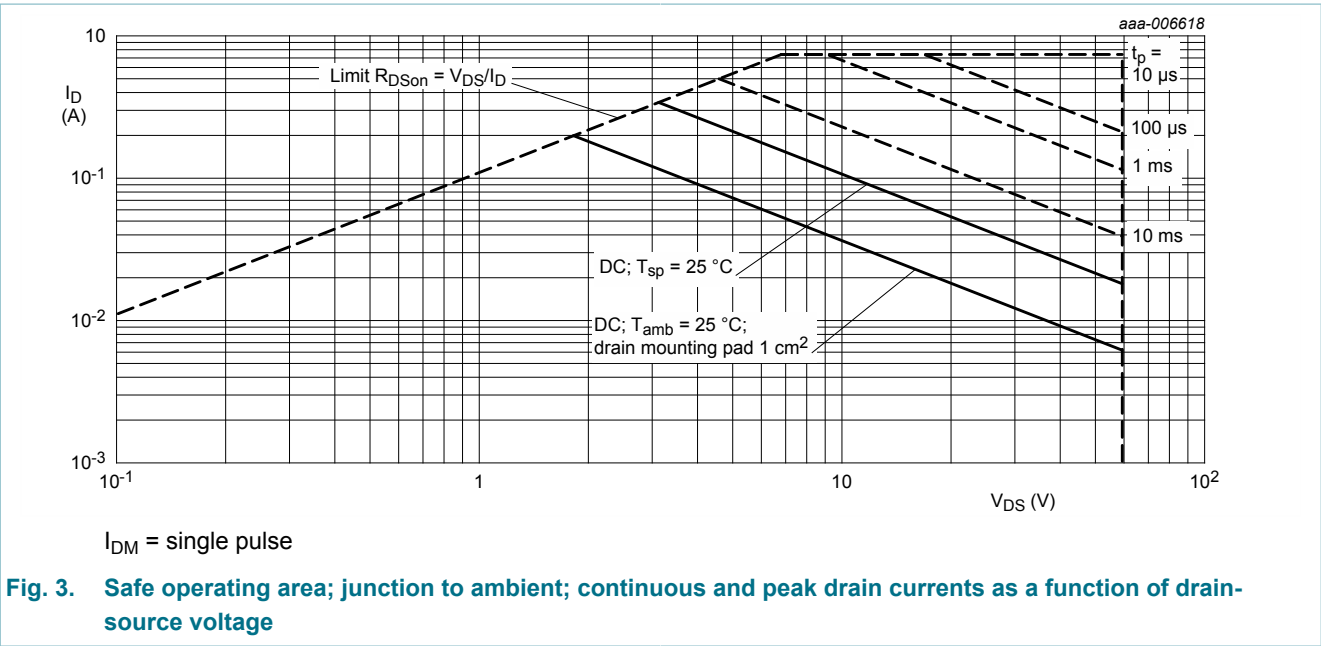


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

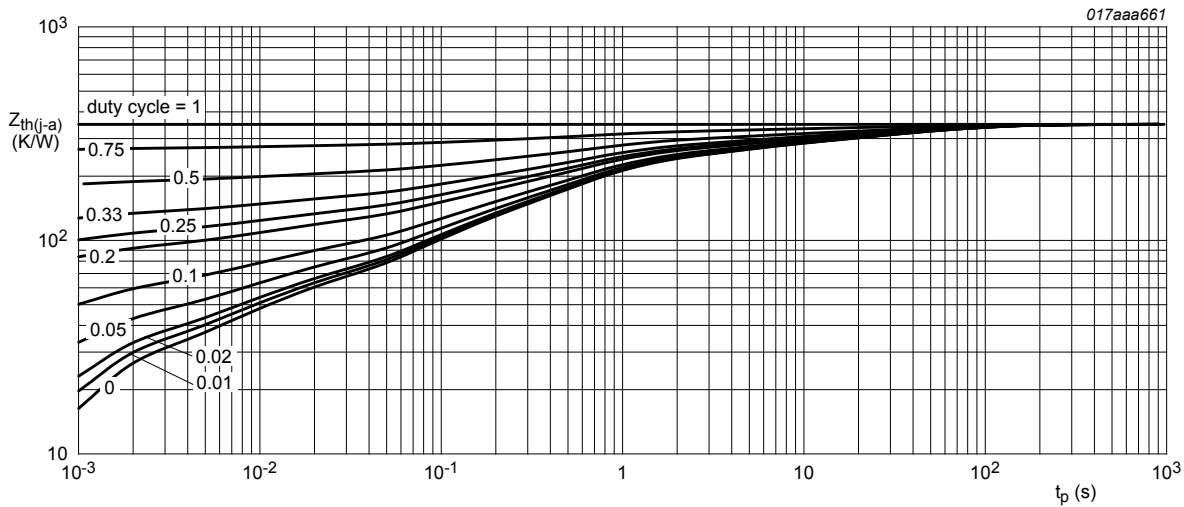


9. Thermal characteristics

Table 6. Thermal characteristics

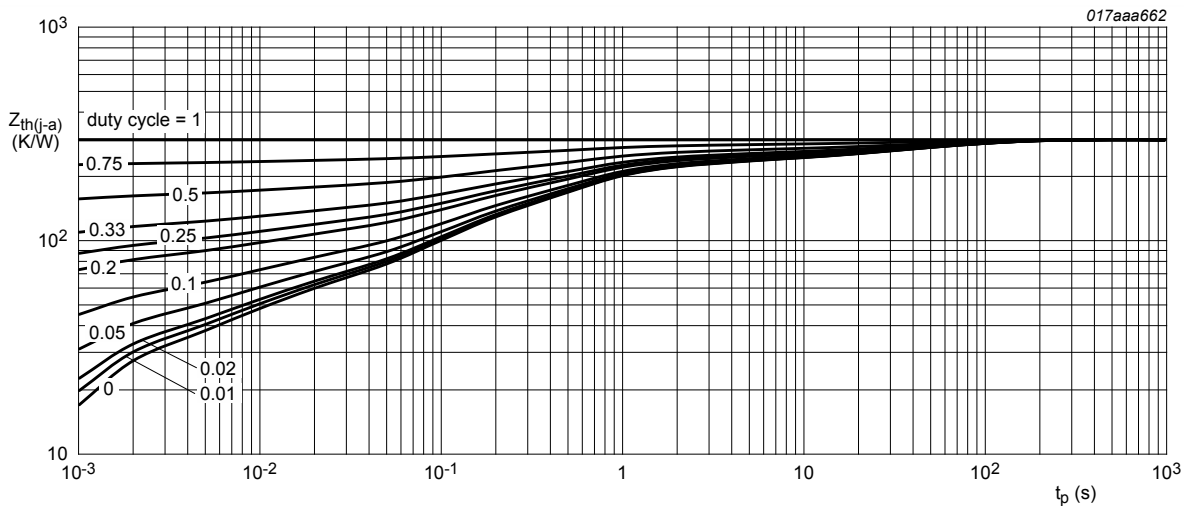
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	350	400	K/W
			[2]	-	300	340	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	115	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 ^\circ C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 A$; $V_{DS} = V_{GS}$; $T_j = 25 ^\circ C$	0.8	1.2	1.5	V
I_{DSS}	drain leakage current	$V_{DS} = 60 V$; $V_{GS} = 0 V$; $T_j = 25 ^\circ C$	-	-	1	μA
		$V_{DS} = 60 V$; $V_{GS} = 0 V$; $T_j = 150 ^\circ C$	-	-	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V$; $V_{DS} = 0 V$; $T_j = 25 ^\circ C$	-	-	3.5	μA
		$V_{GS} = -20 V$; $V_{DS} = 0 V$; $T_j = 25 ^\circ C$	-	-	-3.5	μA
		$V_{GS} = 10 V$; $V_{DS} = 0 V$; $T_j = 25 ^\circ C$	-	-	1	μA
		$V_{GS} = -10 V$; $V_{DS} = 0 V$; $T_j = 25 ^\circ C$	-	-	-1	μA
		$V_{GS} = 4.5 V$; $V_{DS} = 0 V$; $T_j = 25 ^\circ C$	-	-	0.5	μA
		$V_{GS} = -4.5 V$; $V_{DS} = 0 V$; $T_j = 25 ^\circ C$	-	-	-0.5	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 V$; $I_D = 100 mA$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.02$; $T_j = 25 ^\circ C$	-	2.7	4.5	Ω
		$V_{GS} = 10 V$; $I_D = 100 mA$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.02$; $T_j = 150 ^\circ C$	-	5.5	9.2	Ω
		$V_{GS} = 4.5 V$; $I_D = 100 mA$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.02$; $T_j = 25 ^\circ C$	-	3	5.2	Ω
		$V_{GS} = 2.5 V$; $I_D = 10 mA$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.02$; $T_j = 25 ^\circ C$	-	4	13	Ω
g_{fs}	forward transconductance	$V_{DS} = 10 V$; $I_D = 150 mA$; pulsed; $t_p \leq 300 \mu s$; $\delta \leq 0.02$; $T_j = 25 ^\circ C$	320	-	-	mS
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 30 V$; $I_D = 150 mA$; $V_{GS} = 4.5 V$; $T_j = 25 ^\circ C$	-	0.39	0.51	nC
Q_{GS}	gate-source charge		-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C_{iss}	input capacitance	$V_{DS} = 30 V$; $f = 1 MHz$; $V_{GS} = 0 V$; $T_j = 25 ^\circ C$	-	13	20	pF
C_{oss}	output capacitance		-	2.6	-	pF
C_{rss}	reverse transfer capacitance		-	1.1	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 40 V$; $R_L = 250 \Omega$; $V_{GS} = 10 V$; $R_{G(ext)} = 6 \Omega$; $T_j = 25 ^\circ C$	-	5	10	ns
t_r	rise time		-	6	-	ns
$t_{d(off)}$	turn-off delay time		-	36	72	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_f	fall time		-	22	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 115\text{ mA}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$	0.47	0.7	1.2	V

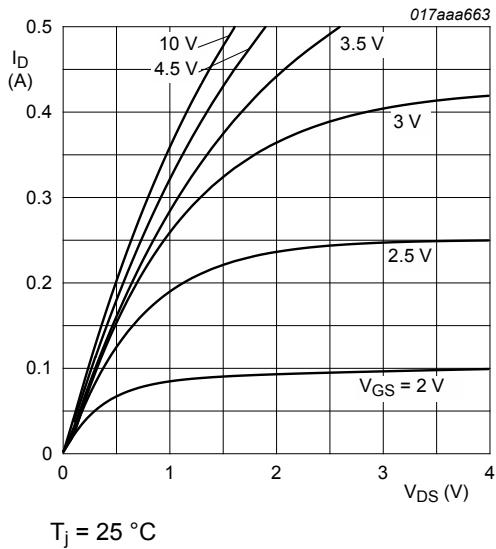


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

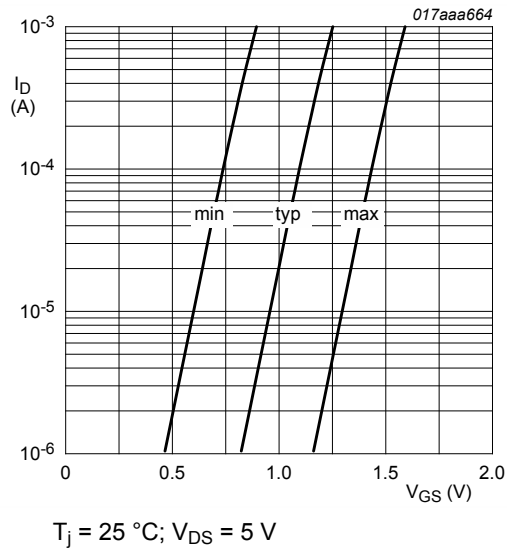


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

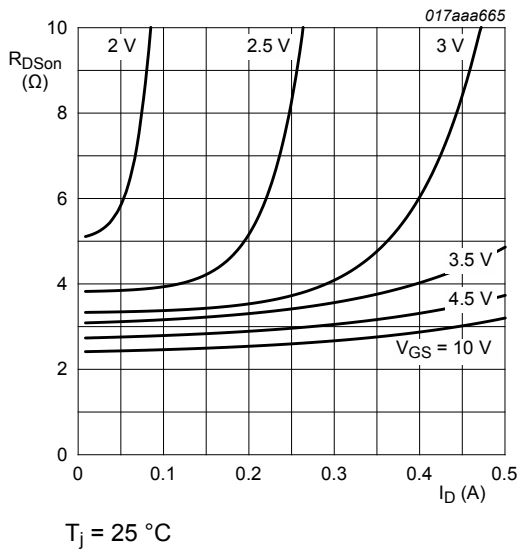


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

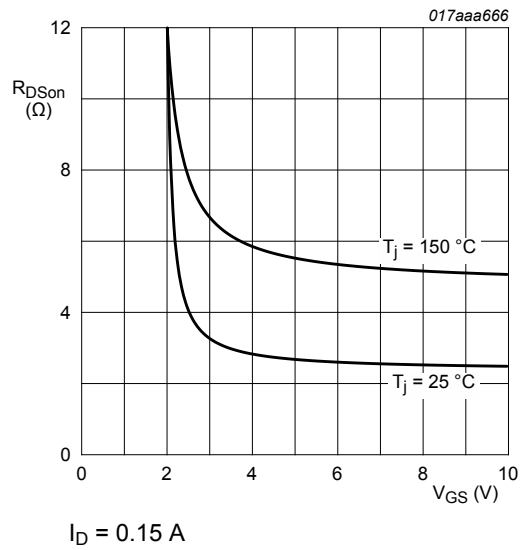


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

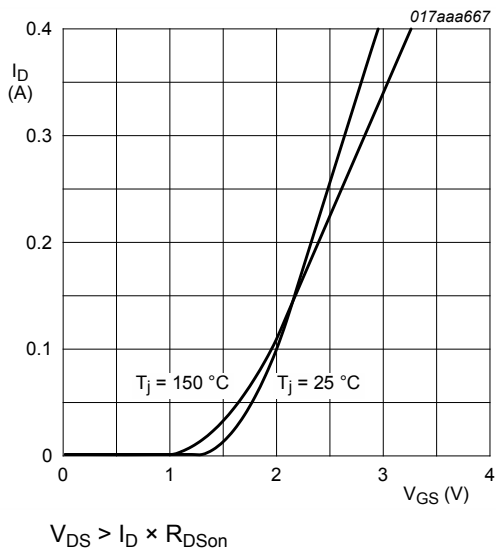


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

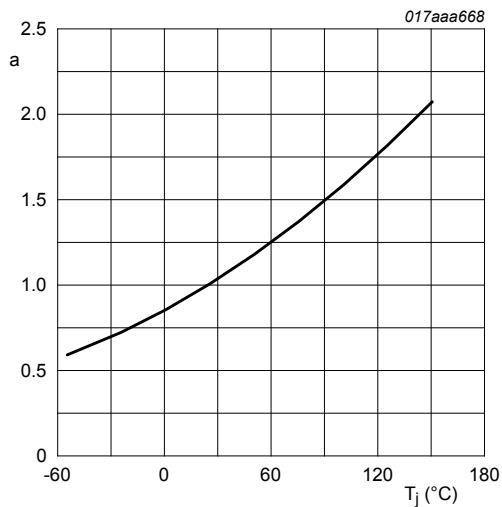


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

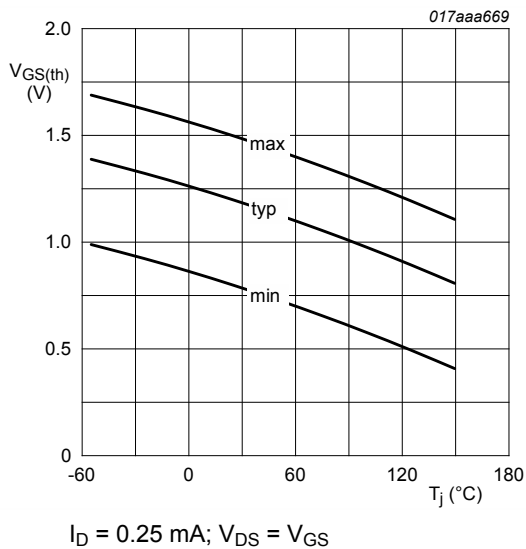


Fig. 12. Gate-source threshold voltage as a function of junction temperature

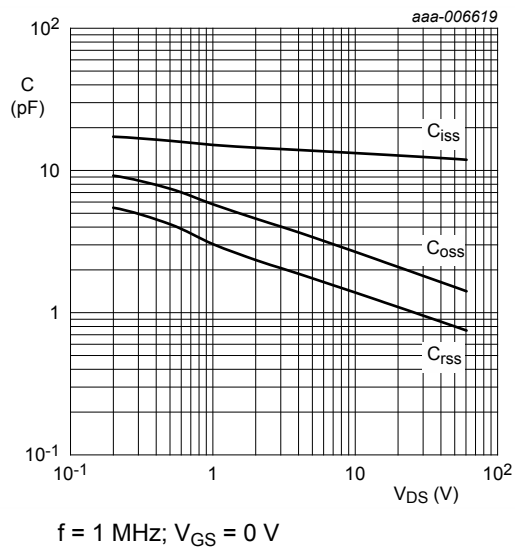


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

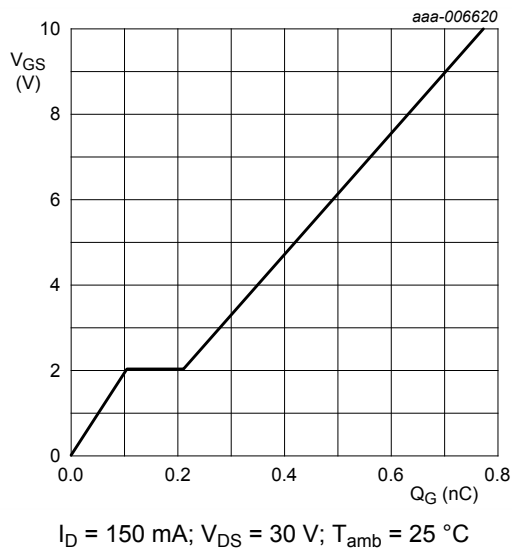


Fig. 14. Gate-source voltage as a function of gate charge; typical values

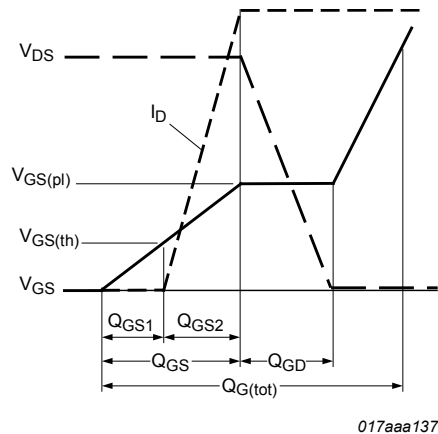


Fig. 15. Gate charge waveform definitions

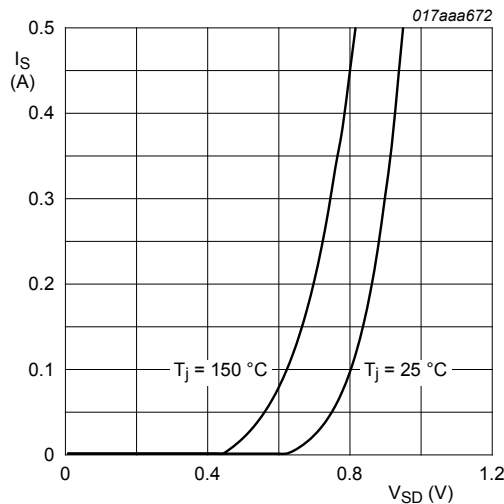


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

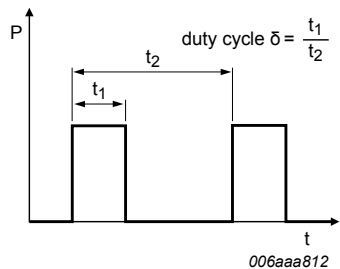
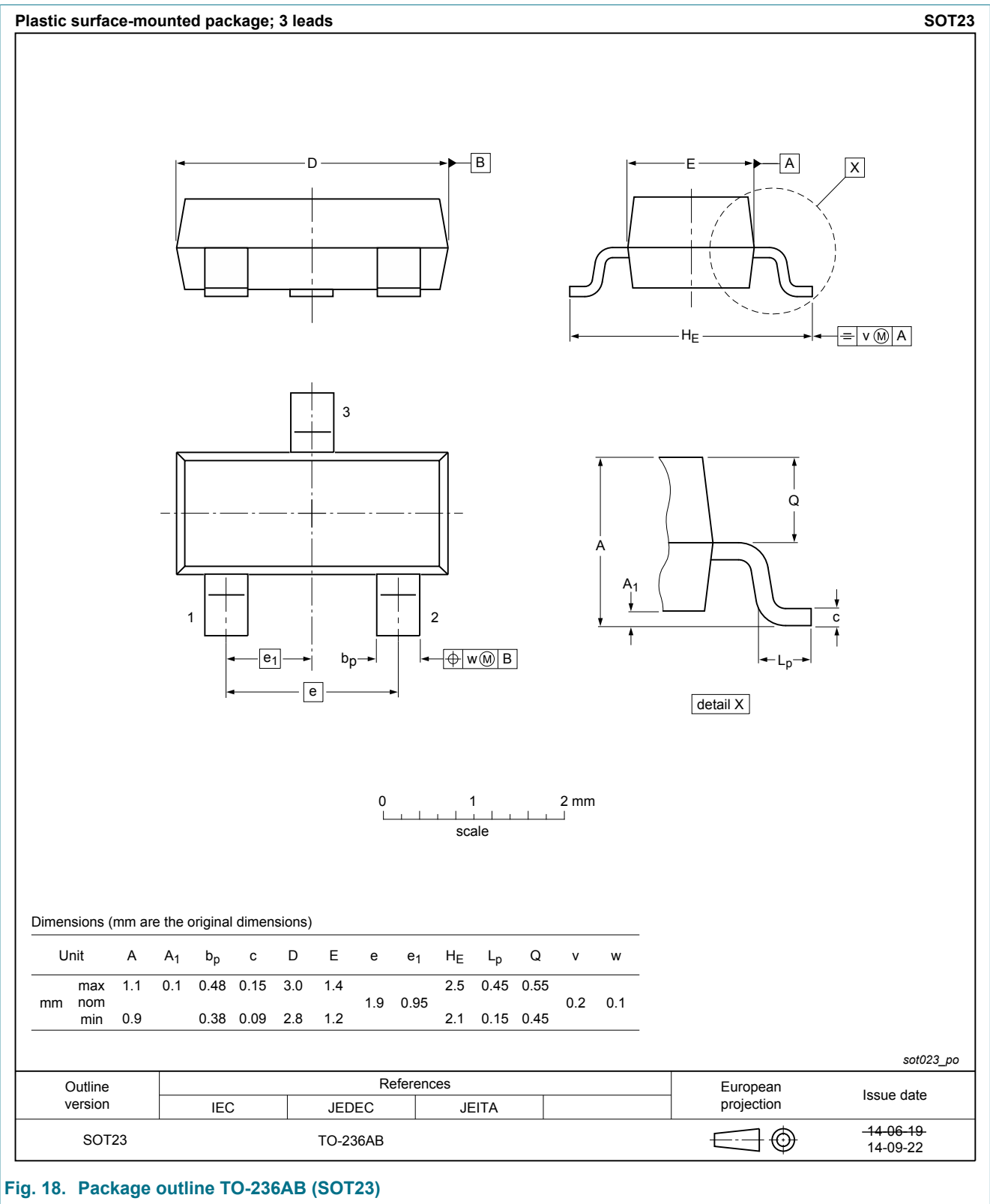


Fig. 17. Duty cycle definition

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering

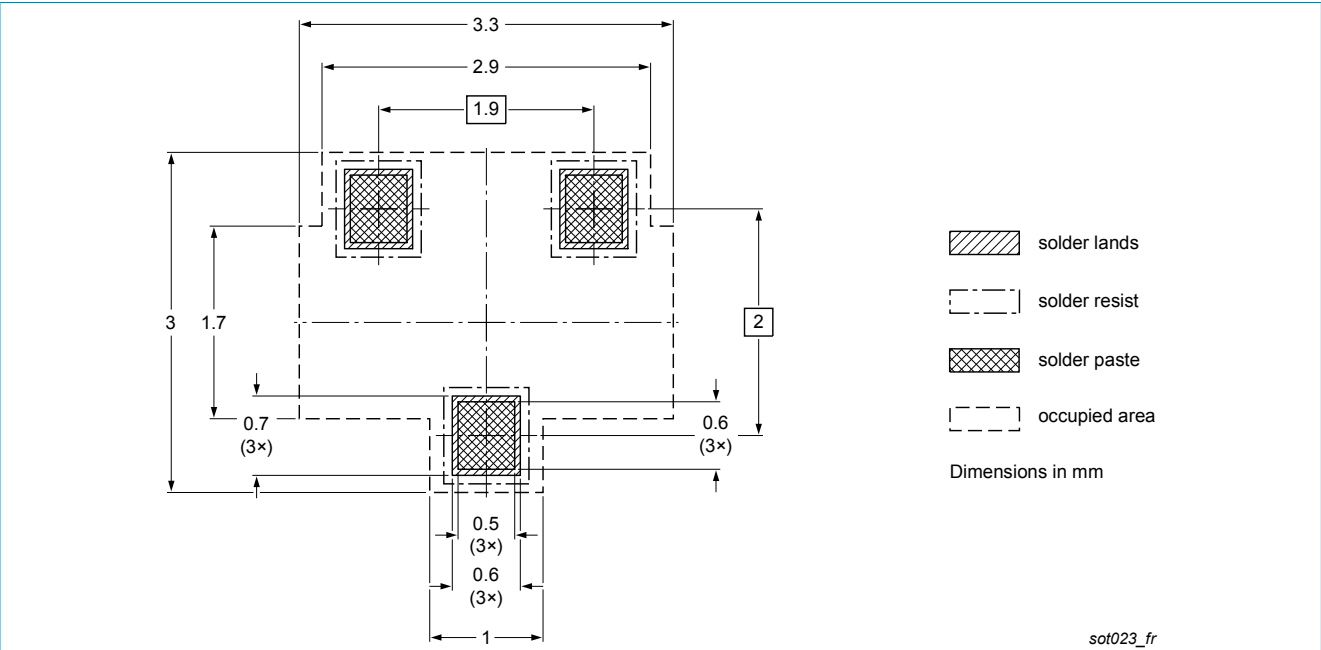


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

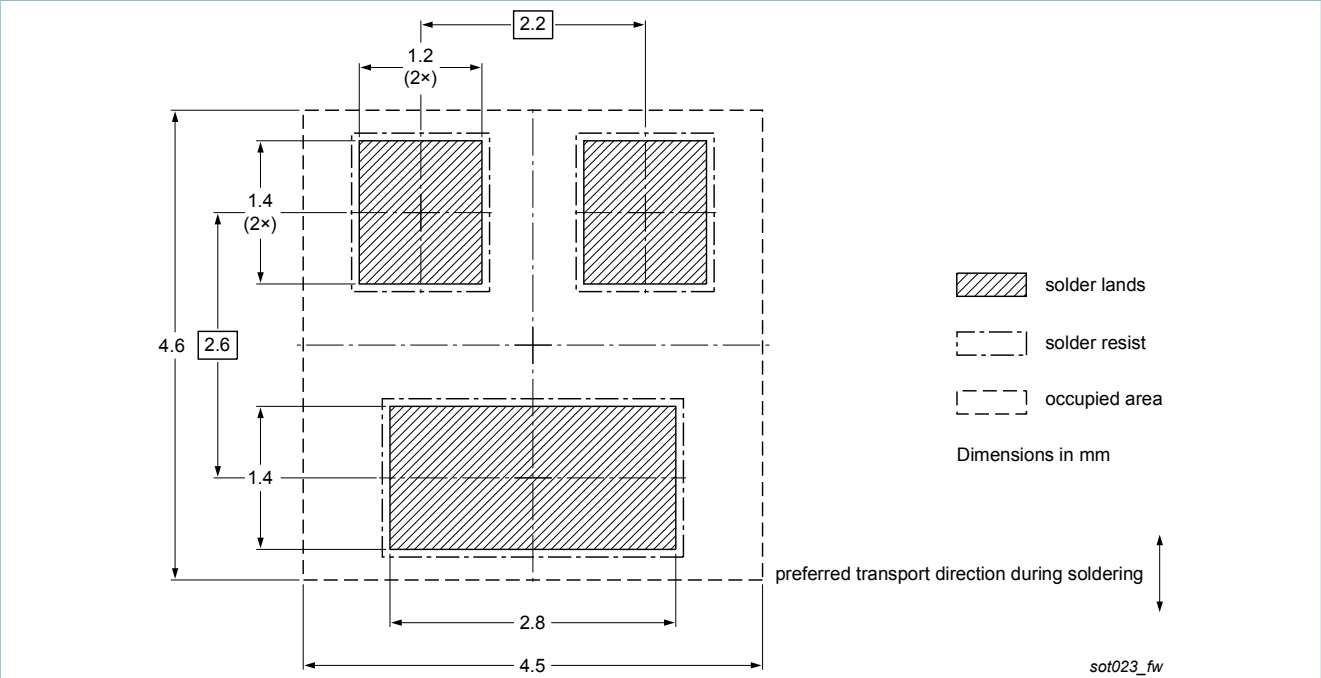


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSS138AKA v.3	20150429	Product data sheet	-	BSS138AKA v.2
Modifications:	Figure 14: x-axis scale corrected			
BSS138AKA v.2	20141103	Product data sheet	-	BSS138AKA v.1
BSS138AKA v.1	20130206	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
11.1	Quality information	10
12	Package outline	11
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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